

DZ4J030K0R

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 3J

■ Basic Part Number :
Dual DZ2J030 (Parallel)

■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±15	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) *1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm)

Solder in (0.8 mm x 0.8 mm)

*2: Test method: IEC61000_4_2(C = 150 pF, R = 330 Ω, Contact discharge: 10 times)

■ Electrical Characteristics $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage ^{*1, *2}	VZ	IZ = 5 mA	2.85		3.15	V
Zener operating resistance	RZ	IZ = 5 mA			120	Ω
Reverse current	IR	VR = 1 V			50	μA
Temperature coefficient of zener voltage ^{*3}	SZ	IZ = 5 mA		-2.0		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

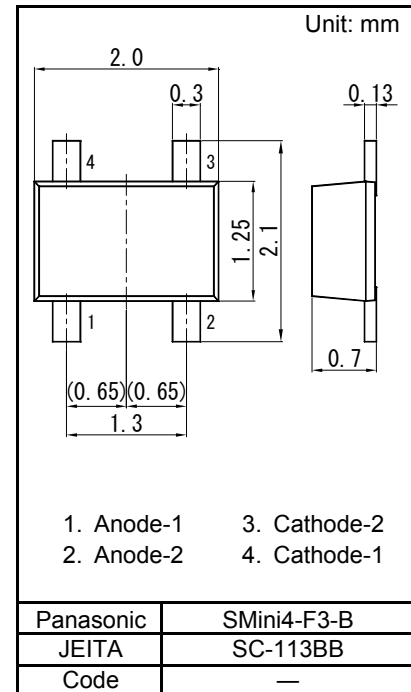
2. Absolute frequency of input and output is 5 MHz.

3. *1: The temperature must be controlled 25 °C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ (25 °C)

*2: VZ guaranteed 20 ms after current flow.

*3: Tj = 25 °C to 150 °C



Internal Connection

